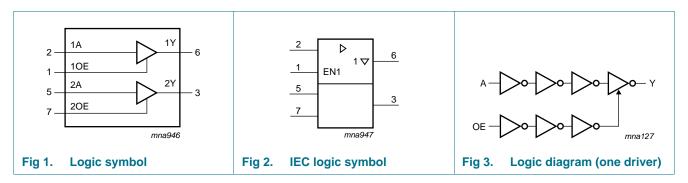
Dual buffer/line driver; 3-state

4. Marking

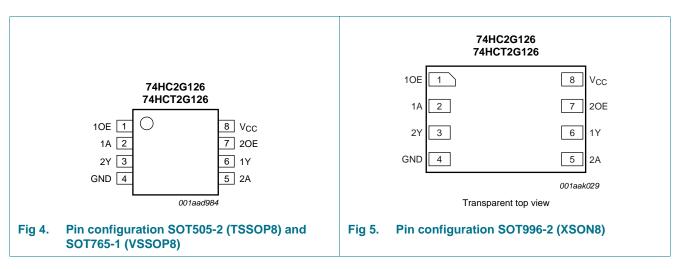
Table 2. Marking codes ^[1]	
Type number	Marking code
74HC2G126DP	H26
74HCT2G126DP	T26
74HC2G126DC	H26
74HCT2G126DC	T26
74HC2G126GD	H26
74HCT2G126GD	T26

[1] The pin 1 indicator is located on the lower left corner of the device, below the marking code.

5. Functional diagram



6. Pinning information



6.1 Pinning

74HC_HCT2G126

6.2 Pin description

Table 3.	Pin description	
Symbol	Pin	Description
10E, 20E	1, 7	output enable input
1A, 2A	2, 5	data input
1Y, 2Y	6, 3	data output
GND	4	ground (0 V)
V _{CC}	8	supply voltage

7. Functional description

Table 4. Function table^[1]

Input nOE		Output
nOE	nA	nY
Н	L	L
Н	Н	Н
L	Х	Z

[1] H = HIGH voltage level; L = LOW voltage level; X = don't care; Z = high-impedance OFF-state.

8. Limiting values

Table 5.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Мах	Unit
V _{CC}	supply voltage		-0.5	+7.0	V
I _{IK}	input clamping current	$V_{\rm I}$ < –0.5 V or $V_{\rm I}$ > $V_{\rm CC}$ + 0.5 V	<u>[1]</u> _	±20	mA
I _{OK}	output clamping current	$V_{\rm O}$ < –0.5 V or $V_{\rm O}$ > $V_{\rm CC}$ + 0.5 V	<u>[1]</u> _	±20	mA
lo	output current	$V_{O} = -0.5 \text{ V}$ to ($V_{CC} + 0.5 \text{ V}$)	<u>[1]</u> _	±35	mA
I _{CC}	supply current		-	70	mA
I _{GND}	ground current		-70	-	mA
T _{stg}	storage temperature		-65	+150	°C
P _{tot}	total power dissipation		[2] _	300	mW

[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] For TSSOP8 package: above 55 °C the value of P_{tot} derates linearly with 2.5 mW/K.

For VSSOP8 package: above 110 °C the value of P_{tot} derates linearly with 8 mW/K.

For XSON8 package: above 118 °C the value of P_{tot} derates linearly with 7.8 mW/K.

Dual buffer/line driver; 3-state

9. Recommended operating conditions

Table 6. Recommended operating conditions

Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	74	74HC2G126			74HCT2G126		
			Min	Тур	Max	Min	Тур	Max	
V _{CC}	supply voltage		2.0	5.0	6.0	4.5	5.0	5.5	V
VI	input voltage		0	-	V _{CC}	0	-	V _{CC}	V
Vo	output voltage		0	-	V_{CC}	0	-	V _{CC}	V
T _{amb}	ambient temperature		-40	+25	+125	-40	+25	+125	°C
Δt/ΔV	input transition rise	$V_{CC} = 2.0 V$	-	-	625	-	-	-	ns/V
â	and fall rate	$V_{CC} = 4.5 V$	-	1.67	139	-	1.67	139	ns/V
		$V_{CC} = 6.0 V$	-	-	83	-	-	-	ns/V

10. Static characteristics

Table 7. Static characteristics

Voltages are referenced to GND (ground = 0 V). All typical values are measured at T_{amb} = 25 °C.

Symbol	Parameter	Conditions	T _{amb} =	–40 °C to	• +85 °C	$T_{amb} = -40$	°C to +125 °C	Unit
			Min	Тур	Max	Min	Max	-
74HC2G1	26			1	1			
V _{IH}	HIGH-level input	V _{CC} = 2.0 V	1.5	1.2	-	1.5	-	V
	voltage	V _{CC} = 4.5 V	3.15	2.4	-	3.15	-	V
		V _{CC} = 6.0 V	4.2	3.2	-	4.2	-	V
V _{IL}	LOW-level input	V _{CC} = 2.0 V	-	0.8	0.5	-	0.5	V
	voltage	V _{CC} = 4.5 V	-	2.1	1.35	-	1.35	V
		V _{CC} = 6.0 V	-	2.8	1.8	-	1.8	V
V _{ОН}	HIGH-level	$V_{I} = V_{IH} \text{ or } V_{IL}$						
	output voltage	I_{O} = -20 μ A; V_{CC} = 2.0 V	1.9	2.0	-	1.9	-	V
		$I_O = -20 \ \mu\text{A}; \ V_{CC} = 4.5 \ \text{V}$	4.4	4.5	-	4.4	-	V
		$I_0 = -20 \ \mu\text{A}; \ V_{CC} = 6.0 \ \text{V}$	5.9	6.0	-	5.9	-	V
		$I_{O} = -6.0 \text{ mA}; V_{CC} = 4.5 \text{ V}$	3.84	4.32	-	3.7	-	V
		$I_0 = -7.8 \text{ mA}; V_{CC} = 6.0 \text{ V}$	5.34	5.81	-	5.2	-	V
V _{OL}	LOW-level output	$V_{I} = V_{IH} \text{ or } V_{IL}$						
	voltage	$I_0 = 20 \ \mu A; \ V_{CC} = 2.0 \ V$	-	0	0.1	-	0.1	V
		$I_0 = 20 \ \mu A; \ V_{CC} = 4.5 \ V$	-	0	0.1	-	0.1	V
		$I_0 = 20 \ \mu A; \ V_{CC} = 6.0 \ V$	-	0	0.1	-	0.1	V
		I_0 = 6.0 mA; V_{CC} = 4.5 V	-	0.15	0.33	-	0.4	V
		I_0 = 7.8 mA; V_{CC} = 6.0 V	-	0.16	0.33	-	0.4	V
l _l	input leakage current	$V_{I} = V_{CC}$ or GND; $V_{CC} = 6.0 V$	-	-	±1.0	-	±1.0	μΑ
I _{OZ}	OFF-state output current	$ \begin{array}{l} V_{I}=V_{IH} \text{ or } V_{IL}; \\ V_{O}=V_{CC} \text{ or } GND; \ V_{CC}=6.0 \ V \end{array} $	-	-	±5.0	-	±10	μΑ

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Dual buffer/line driver; 3-state

Symbol	Parameter	Conditions	T _{amb} =	–40 °C to	• +85 °C	$T_{amb} = -40$ °	°C to +125 °C	Unit
			Min	Тур	Max	Min	Max	
I _{CC}	supply current	$\label{eq:VI} \begin{array}{l} V_{I} = V_{CC} \text{ or } GND; \ I_{O} = 0 \ A; \\ V_{CC} = 6.0 \ V \end{array}$	-	-	10	-	20	μA
CI	input capacitance		-	1.0	-	-	-	pF
Co	output capacitance		-	1.5	-	-	-	pF
74HCT2G	126							
V _{IH}	HIGH-level input voltage	V_{CC} = 4.5 V to 5.5 V	2.0	1.6	-	2.0	-	V
V _{IL}	LOW-level input voltage	V_{CC} = 4.5 V to 5.5 V	-	1.2	0.8	-	0.8	V
V _{OH}	HIGH-level	$V_{I} = V_{IH} \text{ or } V_{IL}; V_{CC} = 4.5 \text{ V}$						
	output voltage	I _O = -20 μA	4.4	4.5	-	4.4	-	V
		$I_{O} = -6.0 \text{ mA}$	3.84	4.32	-	3.7	-	V
V _{OL}		V_{I} = V_{IH} or $V_{\text{IL}};$ V_{CC} = 4.5 V						
	voltage	I _O = 20 μA	-	0	0.1	-	0.1	V
		l _O = 6.0 mA	-	0.16	0.33	-	0.4	V
l _l	input leakage current	$V_{I} = V_{CC}$ or GND; $V_{CC} = 5.5 V$	-	-	±1.0	-	±1.0	μA
I _{OZ}	OFF-state output current	$V_{I} = V_{IH} \text{ or } V_{IL}; V_{O} = V_{CC} \text{ or GND}; V_{CC} = 5.5 \text{ V}$	-	-	±5.0	-	±10	
I _{CC}	supply current	$V_I = V_{CC}$ or GND; $I_O = 0$ A; $V_{CC} = 5.5$ V	-	-	10	-	20	μΑ
ΔI_{CC}	additional supply current	per input; V _{CC} = 4.5 V to 5.5 V; V _I = V _{CC} - 2.1 V; I _O = 0 A	-	-	375	-	410	μΑ
Cı	input capacitance		-	1.0	-	-	-	pF
Co	output capacitance		-	1.5	-	-	-	pF

Static characteristics ... continued Table 7.

11. Dynamic characteristics

Table 8. **Dynamic characteristics**

Voltages are referenced to GND (ground = 0 V); $C_L = 50 \text{ pF}$ unless otherwise specified; for test circuit see Figure 8.

Symbol	Parameter	Conditions		-40 °C to	+85 °C	T _{amb} = -40 °	Unit	
			Min	Typ <mark>[1]</mark>	Max	Min	Max	
74HC2G	126							
t _{pd}	propagation	nA to nY; see Figure 6	2]					
	delay	$V_{CC} = 2.0 V$	-	35	115	-	135	ns
		$V_{CC} = 4.5 V$	-	11	23	-	27	ns
		$V_{CC} = 5.0 \text{ V}; \text{ C}_{L} = 15 \text{ pF}$	-	10	-	-	-	ns
		$V_{CC} = 6.0 V$	-	8	20	-	23	ns

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Dual buffer/line driver; 3-state

Symbol	Parameter	Conditions		T _{amb} =	–40 °C to	+85 °C	$T_{amb} = -40$ °	°C to +125 °C	Unit
				Min	Typ <mark>[1]</mark>	Max	Min	Max	
t _{en}	enable time	nOE to nY; see <u>Figure 7</u>	[2]						
		$V_{CC} = 2.0 V$		-	40	115	-	135	ns
		$V_{CC} = 4.5 V$		-	11	23	-	27	ns
		$V_{CC} = 6.0 V$		-	8	20	-	23	ns
t _{dis}	disable time	nOE to nY; see <u>Figure 7</u>	[2]						
		$V_{CC} = 2.0 V$		-	25	125	-	150	ns
		$V_{CC} = 4.5 V$		-	12	25	-	30	ns
		$V_{CC} = 6.0 V$		-	10	21	-	26	ns
t _t	transition	nY; see <u>Figure 6</u>	[2]						
	time	$V_{CC} = 2.0 V$		-	18	75	-	90	ns
		$V_{CC} = 4.5 V$		-	6	15	-	18	ns
		$V_{CC} = 6.0 V$		-	5	13	-	15	ns
C _{PD}	power	per buffer; $V_I = GND$ to V_{CC}	[3]						
	dissipation capacitance	output enabled		-	11	-	-	-	pF
	capacitance	output disabled		-	1	-	-	-	pF
74HCT2	G126								
t _{pd}	propagation	nA to nY; see <u>Figure 6</u>	[2]						
	delay	$V_{CC} = 4.5 V$		-	15	30	-	36	ns
		$V_{CC} = 5.0 \text{ V}; \text{ C}_{L} = 15 \text{ pF}$		-	12	-	-	-	ns
t _{en}	enable time	nOE to nY; see <u>Figure 7;</u> V _{CC} = 4.5 V	[2]	-	11	31	-	38	ns
t _{dis}	disable time	nOE to nY; see <u>Figure 7</u> ; $V_{CC} = 4.5 V$	[2]	-	11	35	-	42	ns
t _t	transition time	nY; see <u>Figure 6</u> ; V_{CC} = 4.5 V	[2]	-	6	15	-	18	ns
C _{PD}	power dissipation	per buffer; V _I = GND to V _{CC} – 1.5 V	<u>[3]</u>						
	capacitance	output enabled		-	11	-	-	-	pF
		output disabled			1	-	-	-	pF

Table 8. Dynamic characteristics ...continued

Voltages are referenced to GND (ground = 0 V); $C_L = 50 \text{ pF}$ unless otherwise specified; for test circuit see Figure 8

[1] All typical values are measured at T_{amb} = 25 °C.

[3] C_{PD} is used to determine the dynamic power dissipation (P_D in μ W).

 $\mathsf{P}_{\mathsf{D}} = \mathsf{C}_{\mathsf{P}\mathsf{D}} \times \mathsf{V}_{\mathsf{C}\mathsf{C}}^2 \times \mathsf{f}_i \times \mathsf{N} + \Sigma(\mathsf{C}_{\mathsf{L}} \times \mathsf{V}_{\mathsf{C}\mathsf{C}}^2 \times \mathsf{f}_o) \text{ where:}$

 f_i = input frequency in MHz;

 $f_o = output frequency in MHz;$

 C_L = output load capacitance in pF;

 V_{CC} = supply voltage in V;

N = number of inputs switching;

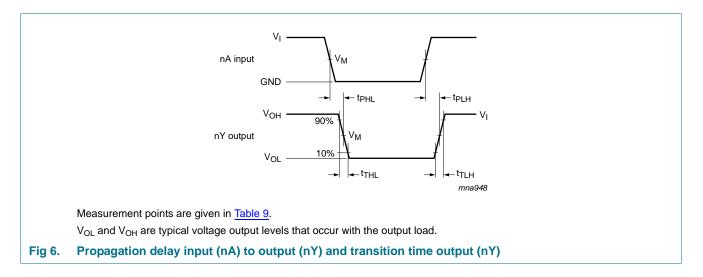
 $\Sigma(C_L \times V_{CC}{}^2 \times f_o)$ = sum of outputs.

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Dual buffer/line driver; 3-state

12. Waveforms



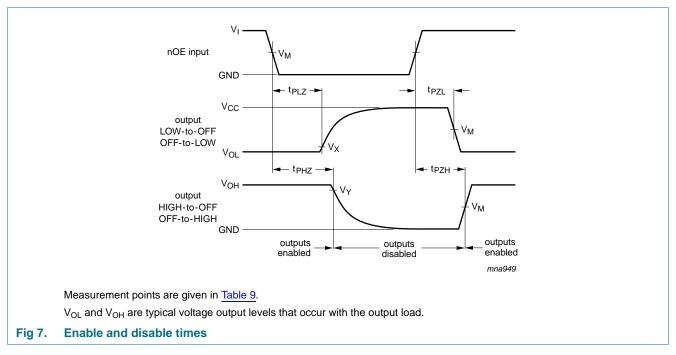


Table 9. Measurement points

Туре	Input	Output				
	V _M	V _M	V _X	V _Y		
74HC2G126	0.5V _{CC}	0.5V _{CC}	V _{OL} + 0.3 V	V _{OH} – 0.3 V		
74HCT2G126	1.3 V	1.3 V	V _{OL} + 0.3 V	V _{OH} – 0.3 V		

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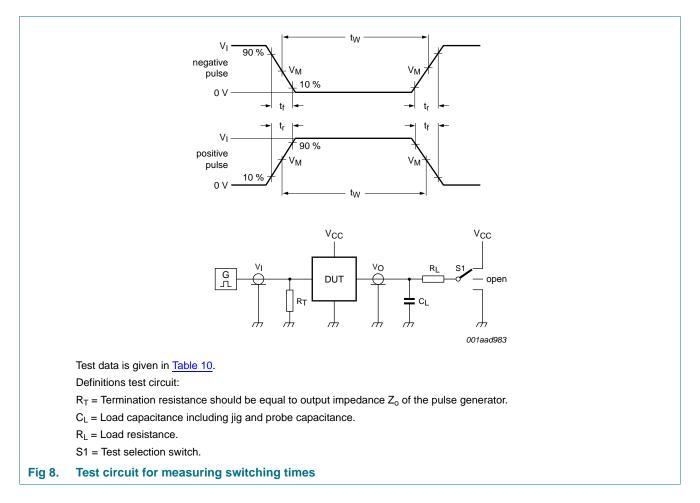


Table 10. Test data

Туре	Input		Load		S1 position		
	VI	t _r , t _f	CL	RL	t _{PHL} , t _{PLH}	t _{PZH} , t _{PHZ}	t _{PZL} , t _{PLZ}
74HC2G126	GND to V_{CC}	\leq 6 ns	15 pF, 50 pF	1 kΩ	open	GND	V _{CC}
74HCT2G126	GND to 3 V	\leq 6 ns	15 pF, 50 pF	1 kΩ	open	GND	V _{CC}

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13. Package outline

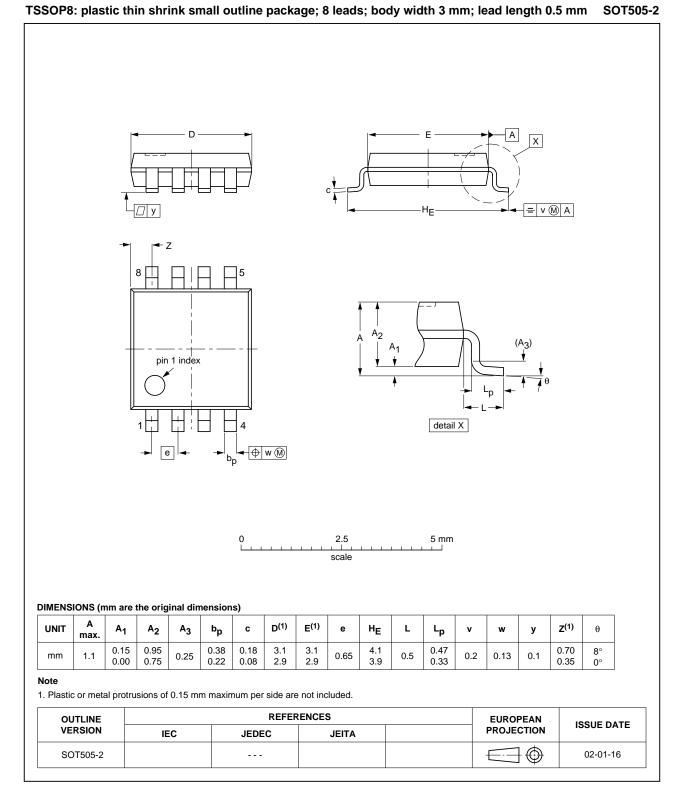


Fig 9. Package outline SOT505-2 (TSSOP8)

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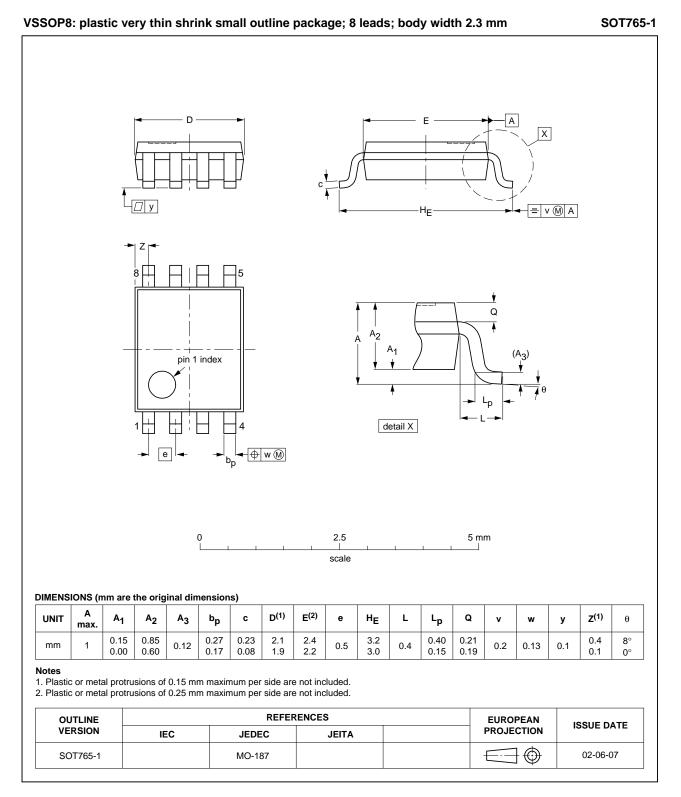


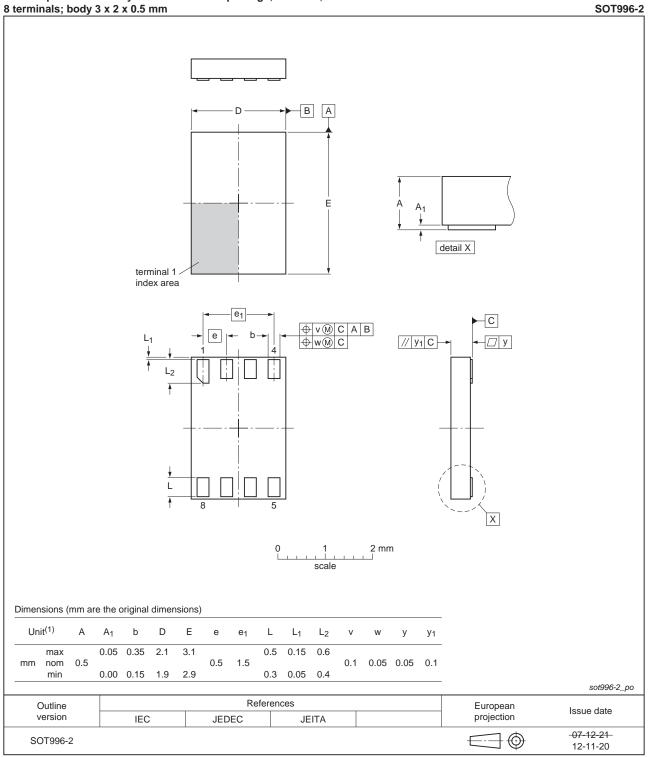
Fig 10. Package outline SOT765-1 (VSSOP8)

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XSON8: plastic extremely thin small outline package; no leads; 8 terminals: body 3 x 2 x 0.5 mm

Fig 11. Package outline SOT996-2 (XSON8)

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14. Abbreviations

AcronymDescriptionCMOSComplementary Metal Oxide SemiconductorDUTDevice Under TestESDElectroStatic DischargeHBMHuman Body ModelMMMachine Model	Table 11. Abbreviations			
DUTDevice Under TestESDElectroStatic DischargeHBMHuman Body Model	Acronym	Description		
ESD ElectroStatic Discharge HBM Human Body Model	CMOS	Complementary Metal Oxide Semiconductor		
HBM Human Body Model	DUT	Device Under Test		
	ESD	ElectroStatic Discharge		
MM Machine Model	HBM	Human Body Model		
	MM	Machine Model		

15. Revision history

Table 12.Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74HC_HCT2G126 v.5	20131218	Product data sheet	-	74HC_HCT2G126 v.4
Modifications:	 For type nur 	mbers 74HC2G126GD and 7	4HCT2G126GD XSON	I8U has changed to XSON8.
74HC_HCT2G126 v.4	20090924	Product data sheet	-	74HC_HCT2G126 v.3
Modifications:	• <u>Table 2</u> : Mai	rking codes table added.		
74HC_HCT2G126 v.3	20090507	Product data sheet	-	74HC_HCT2G126 v.2
74HC_HCT2G126 v.2	20051215	Product data sheet	-	74HC_HCT2G126 v.1
74HC_HCT2G126 v.1	20030303	Product data sheet	-	-

16. Legal information

16.1 Data sheet status

Document status[1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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Product data sheet

Dual buffer/line driver; 3-state

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Product data sheet

Dual buffer/line driver; 3-state

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